

## FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR  
APPLICANT'S INFORMATION  
DISCLOSURE STATEMENT

Applicant(s): Allen et al.  
 Docket No.: YOR920030175US1  
 Serial No.: 10/661,041  
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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	FILING DATE IF APPROPRIATE
	6,316,167	11/13/01	Angelopoulos et al.	430/313	

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	TRANSLATION YES NO	

## OTHER DOCUMENTS

EXAMINER INITIAL	REF NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
<u>ca</u>		Chun et al., "Contact Hole Size Reducing Methods by Using Water-Soluble Organic Over-Coating Material (WASOOM) as a Barrier Layer Toward 0.15 um Contact Hole; Resist Flow Technique I," Proc. SPIE, Vol. 3999, pgs. 620-626 (2000).
<u>ca</u>		Chung et al., "A Novel Resist Material for sub-100 nm Contact Hole Pattern," Proc. SPIE, Vol. 3999, pgs. 305-312 (2000).
<u>Ca</u>		DellaGuardia et al., "193 Lithography and RELACST <sup>TM</sup> Processing for BEOL Lithography," Proc. SPIE, Vol. 4346, pgs. 1029-1040 (2001).
<u>ca</u>		Lucas et al., "193 nm Contact Photoresist Reflow Feasibility Study," Proc. SPIE, Vol. 4345, pgs. 725-736 (2001).
<u>Ca</u>		Satou et al., "Sub-0.10 um Hole Fabrication Using Bilayer Silylation Process for 193 nm Lithography," Jpn. J. Appl. Phys. 1, Vol. 38, Part 1, No. 12B, pgs 7008-7012 (December 1999).

Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.